

CMWSH-4
SURFACE MOUNT
SUPERmini™
DUAL ISOLATED
SILICON SCHOTTKY DIODES

SUPERmini™



SOT-343 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMWSH-4, 40V, Low V_F , consists of two galvanically isolated SUPERmini™ Silicon Schottky diodes. The CMWSH-4 has been designed for use in high speed surface mount switching applications.

MARKING CODE: WSH4

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

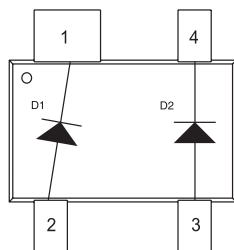
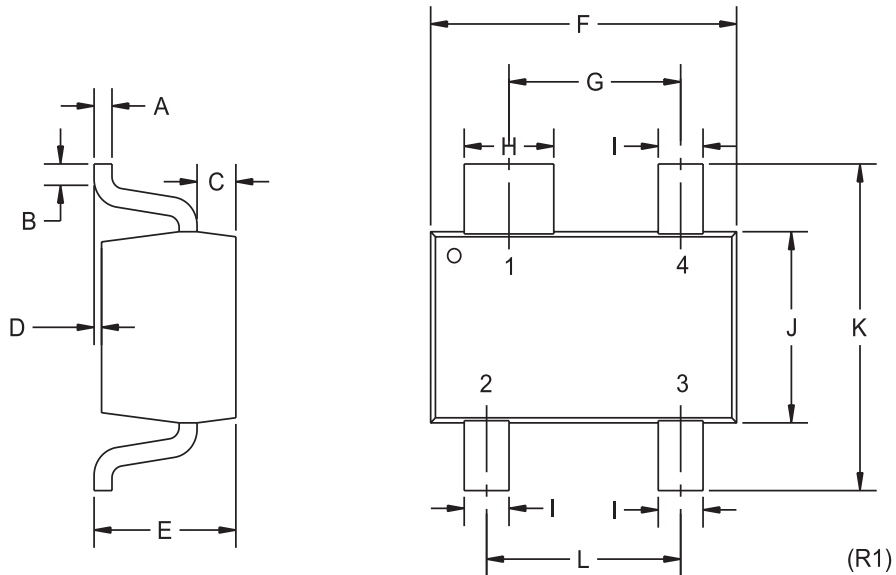
	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
Continuous Forward Current	I_F	100	mA
Peak Repetitive Forward Current	I_{FRM}	350	mA
Forward Surge Current, $t_p=10$ ms	I_{FSM}	750	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_R	$V_R=25\text{V}$		90	500	nA
I_R	$V_R=25\text{V}, T_A=100^\circ\text{C}$		25	100	μA
I_R	$V_R=40\text{V}$		0.23	5.0	μA
V_F	$I_F=2.0\text{mA}$		0.29	0.33	V
V_F	$I_F=15\text{mA}$		0.40	0.45	V
V_F	$I_F=100\text{mA}$		0.52	0.60	V
C_T	$V_R=1.0\text{V}, f=1.0\text{MHz}$		10.0		pF
t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=1.0\text{mA}, R_L=100\Omega$			5.0	ns

R1 (14-November 2002)

SOT-343 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) CATHODE D1
- 2) ANODE D1
- 3) ANODE D2
- 4) CATHODE D2

MARKING CODE: WSH4

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A		0.005		0.12
B		0.006		0.15
C	0.010	0.011	0.26	0.29
D	0.001	0.003	0.03	0.07
E	0.034	0.037	0.87	0.93
F		0.081		2.05
G		0.045		1.15
H	0.022	0.025	0.57	0.63
I	0.011	0.013	0.27	0.33
J	0.047	0.049	1.20	1.25
K	0.079	0.085	2.00	2.15
L		0.051		1.30

SOT-343 (REV: R1)

R1 (14-November 2002)